

Medium Power Transistor (32V, 0.5A)

2SC2411K / 2SC4097 / 2SC1741S

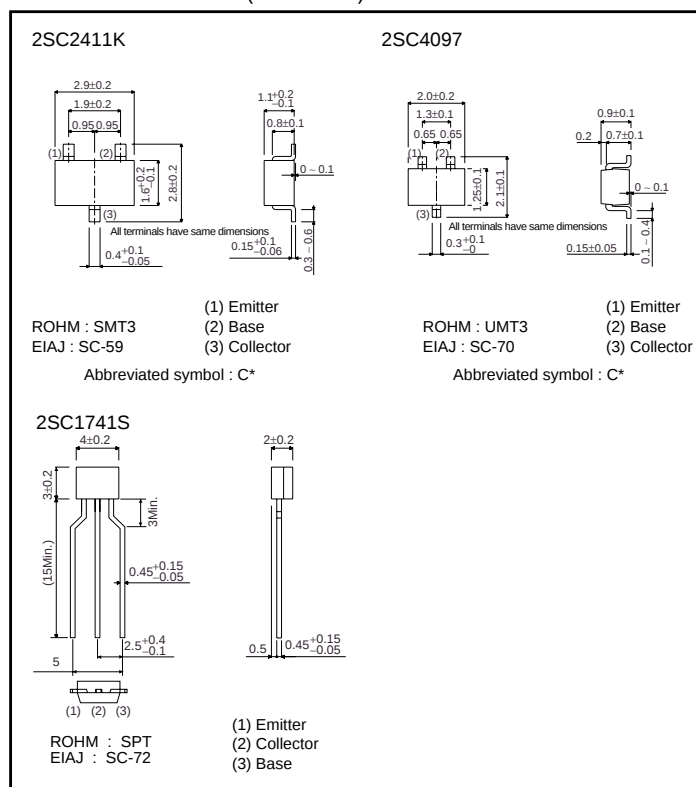
●Features

- 1) High $I_{CMax.}$
 $I_{CMax.} = 0.5mA$
- 2) Low $V_{CE(sat)}$.
Optimal for low voltage operation.
- 3) Complements the
2SA1036K / 2SA1577 / 2SA854S.

●Structure

Epitaxial planar type
NPN silicon transistor

●External dimensions (Units : mm)



* Denotes h_{FE}

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	32	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	0.5	A *
Collector power dissipation	P_C	0.2	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

* P_C must not be exceeded.

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●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	40	—	—	V	$I_C = 100\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	32	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E = 100\mu A$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 20V$
Emitter cutoff current	I_{EBO}	—	—	1	μA	$V_{EB} = 4V$
DC current transfer ratio	2SC2411K, 2SC4097	82	—	390	—	$V_{CE} = 3V, I_C = 100mA$
	2SC1741S	120	—	560	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	$I_C/I_B = 500mA/50mA$
Transition frequency	f_T	—	250	—	MHz	$V_{CE} = 5V, I_E = -20mA, f = 100MHz$
Output capacitance	C_{ob}	—	6.0	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

●Packaging Specifications and hFE

Type	hFE	Package	Taping		
		Code	T146	T106	TP
		Basic ordering unit (pieces)	3000	3000	5000
2SC2411K	PQR		○	—	—
2SC4097	PQR		—	○	—
2SC1741S	QRS		—	—	○

hFE values are classified as follows:

Item	P	Q	R	S
hFE	82 ~ 180	120 ~ 270	180 ~ 390	270 ~ 560

●Electrical characteristic curves

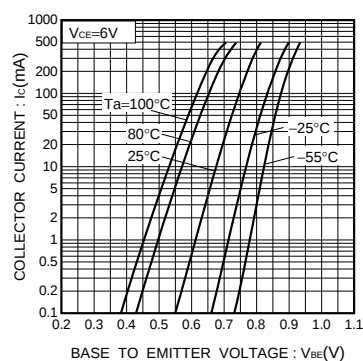


Fig.1 Grounded emitter propagation characteristics

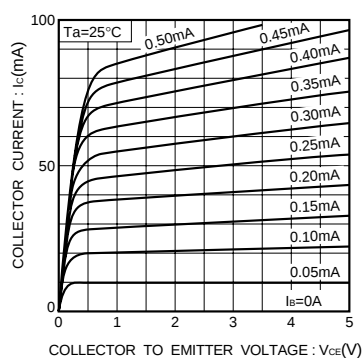


Fig.2 Grounded emitter output characteristics(I)

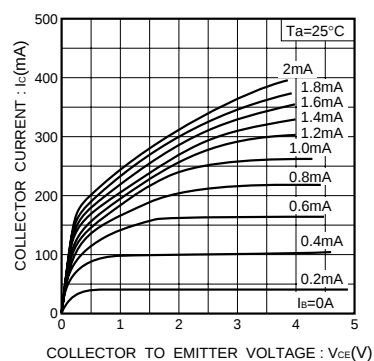


Fig.3 Grounded emitter output characteristics(II)

Transistors

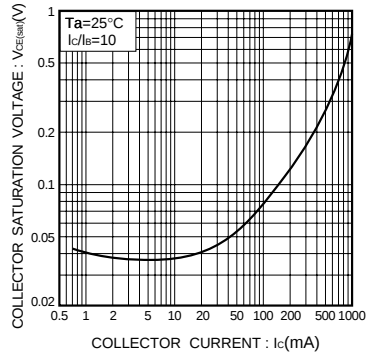


Fig.4 Collector-emitter saturation voltage vs. collector current

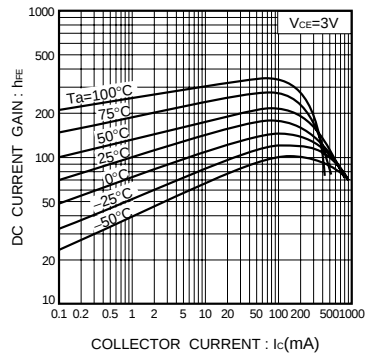


Fig.5 DC current gain vs. collector current

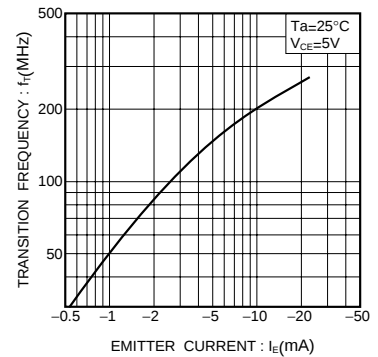


Fig.6 Gain bandwidth product vs. emitter current

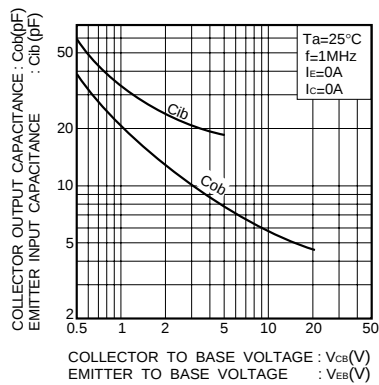


Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage